

SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary we will further optimize the design of our InP laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements. Grin Lens $f=171\mu\text{m}$ used to match fast axis divergence to slow axis divergence. Tall Cap used.



TO-9 Packaged Laser Diode

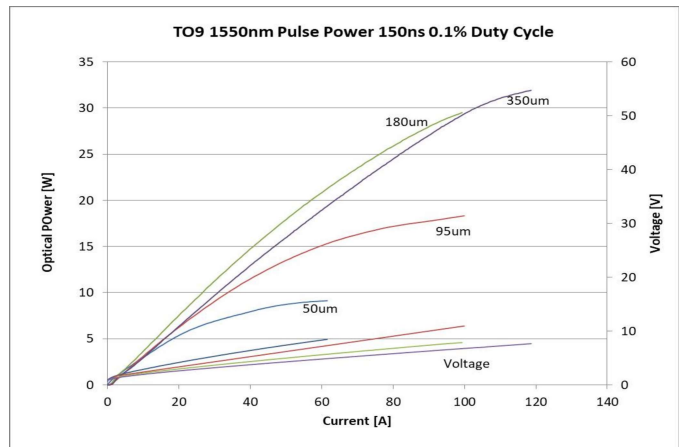
High Power Single-Mode and Multi-Mode SemiNex Lasers
12xx to 19xx nm
Custom Wavelengths Available
Lensed Options Available

Applications

- OEM Medical
- Professional Medical
- LiDAR
- Military / Aerospace
- Illumination

Features

- Cost effective
- High Output Power
- High Dynamic Range
- High Efficiency
- Standard Low Cost Package
- Fast axis divergence matched to slow axis
- Tall Cap used.

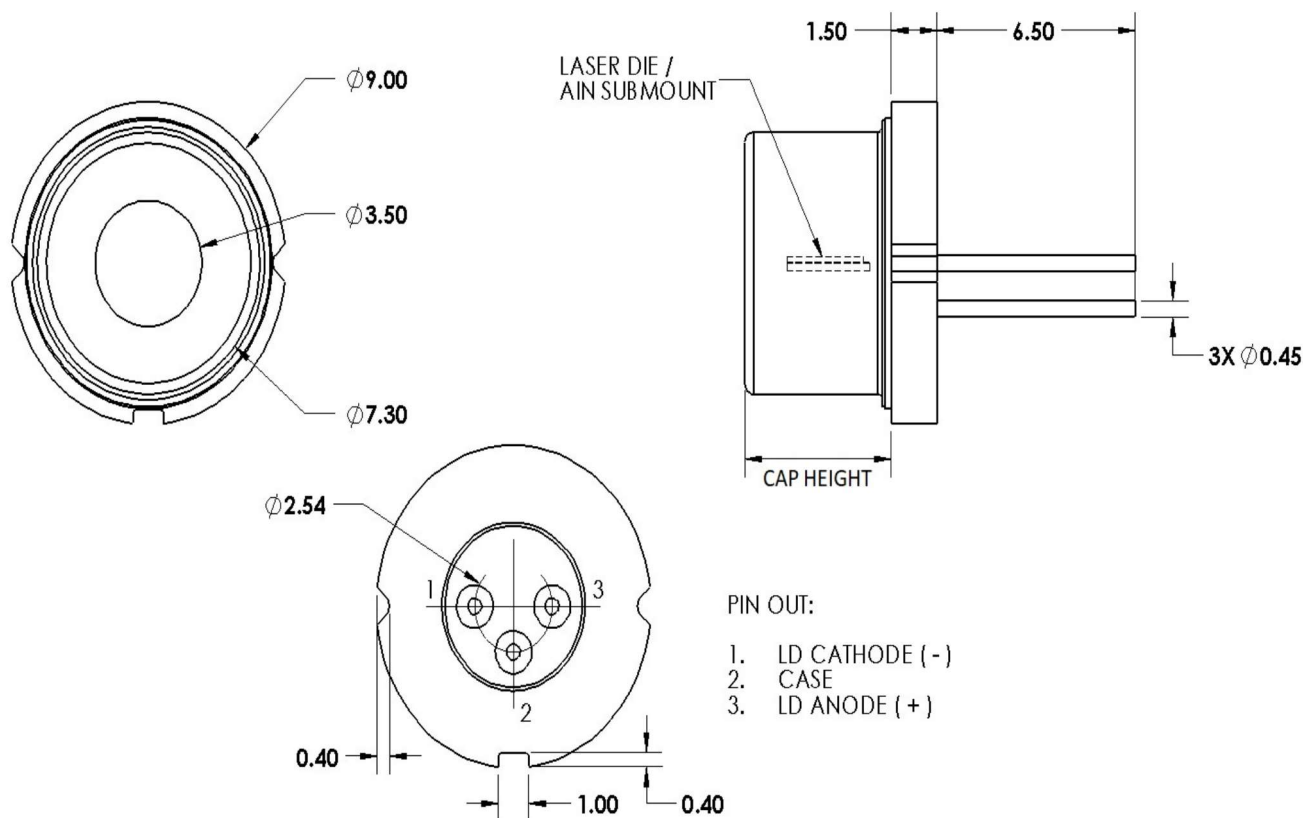




| | Symbol | TO9-148-139 | Units |
|-----------------------|----------------------------|-------------|------------------|
| Optical | | | |
| Wavelength | λ_c | 1565 | nm (± 20) |
| Output Power (Pulsed) | P_o | 24.00 | watts |
| Chip Cavity Length | CL | 2500 | μm |
| Emitter Width | W | 180 | μm |
| Emitter Height | H | 1 | μm |
| Spectral Width | $\delta\lambda$ | 15 | nm 3dB |
| Slope Efficiency | η° | 0.25 | W/A |
| Fast Axis Div.* | Θ_{perp} | 14 | deg FWHM |
| Slow Axis Div. | Θ_{parallel} | 14 | deg FWHM |
| Electrical | | | |
| Power Conversion Eff. | η | 3 | % |
| Operating Current | I_{op} | 80 | A |
| Threshold Current | I_{th} | 1 | A |
| Operating Voltage | V_{op} | 9.5 | V |
| Series Resistance | R_s | 0.14 | ohm |
| Mechanical | | | |
| Weight | | 1.5 | g |
| Operating Temp.** | | -40 to 60 | $^\circ\text{C}$ |
| Storage Temp. | | -40 to 80 | $^\circ\text{C}$ |

Specified values are rated at a constant heat sink temperature of 20°C.
 **Specified operating conditions are based on 20°C heat sink temperature. High temperature operation will reduce performance and MTTF.

Unless otherwise indicated all values are nominal.
 Uncapped TO9 specifications assume heatsinking underneath laser chip.
 Capped TO9 specifications assume heatsinking only on flat surface where pins extend.
 *Pulsed Power measured at 150ns pulse width and 0.1% duty cycle.



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